

Thyristor Module

$$V_{RRM} = 2 \times 1200 \text{ V}$$

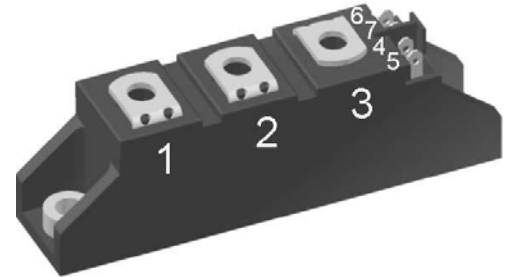
$$I_{TAV} = 110 \text{ A}$$

$$V_T = 1.21 \text{ V}$$


Phase leg

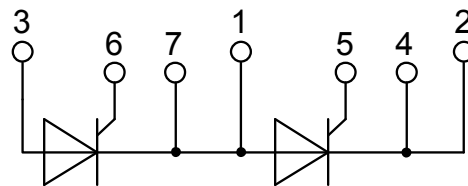
Part number

MCMA110P1200TA



Backside: isolated

 E72873



Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al₂O₃-ceramic

Applications:

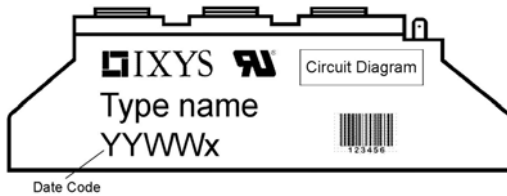
- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package: TO-240AA

- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

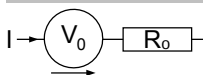
Thyristor				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$			1300	V	
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$			1200	V	
I_{RD}	reverse current, drain current	$V_{RD} = 1200\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$		100	μA	
		$V_{RD} = 1200\text{ V}$	$T_{VJ} = 140^{\circ}\text{C}$		10	mA	
V_T	forward voltage drop	$I_T = 110\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$		1.24	V	
		$I_T = 220\text{ A}$			1.52	V	
		$I_T = 110\text{ A}$	$T_{VJ} = 125^{\circ}\text{C}$		1.21	V	
		$I_T = 220\text{ A}$			1.57	V	
I_{TAV}	average forward current	$T_C = 85^{\circ}\text{C}$	$T_{VJ} = 140^{\circ}\text{C}$		110	A	
$I_{T(RMS)}$	RMS forward current	180° sine			170	A	
V_{T0}	threshold voltage	} for power loss calculation only	$T_{VJ} = 140^{\circ}\text{C}$		0.85	V	
r_T	slope resistance				3.3	m Ω	
R_{thJC}	thermal resistance junction to case				0.3	K/W	
R_{thCH}	thermal resistance case to heatsink			0.20		K/W	
P_{tot}	total power dissipation		$T_C = 25^{\circ}\text{C}$		380	W	
I_{TSM}	max. forward surge current	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}\text{C}$		1.90	kA	
		t = 8,3 ms; (60 Hz), sine	$V_R = 0\text{ V}$		2.05	kA	
		t = 10 ms; (50 Hz), sine	$T_{VJ} = 140^{\circ}\text{C}$		1.62	kA	
		t = 8,3 ms; (60 Hz), sine	$V_R = 0\text{ V}$		1.75	kA	
I^2t	value for fusing	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}\text{C}$		18.1	kA ² s	
		t = 8,3 ms; (60 Hz), sine	$V_R = 0\text{ V}$		17.5	kA ² s	
		t = 10 ms; (50 Hz), sine	$T_{VJ} = 140^{\circ}\text{C}$		13.0	kA ² s	
		t = 8,3 ms; (60 Hz), sine	$V_R = 0\text{ V}$		12.7	kA ² s	
C_J	junction capacitance	$V_R = 400\text{ V}$ f = 1 MHz	$T_{VJ} = 25^{\circ}\text{C}$		95	pF	
P_{GM}	max. gate power dissipation	$t_p = 30\text{ }\mu\text{s}$	$T_C = 140^{\circ}\text{C}$		10	W	
		$t_p = 300\text{ }\mu\text{s}$			5	W	
P_{GAV}	average gate power dissipation				0.5	W	
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 140^{\circ}\text{C}$; f = 50 Hz	repetitive, $I_T = 330\text{ A}$		150	A/ μs	
		$t_p = 200\text{ }\mu\text{s}$; $di_G/dt = 0.45\text{ A}/\mu\text{s}$; $I_G = 0.45\text{ A}$; $V_D = \frac{2}{3} V_{DRM}$	non-repet., $I_T = 110\text{ A}$		500	A/ μs	
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V_D = \frac{2}{3} V_{DRM}$ $R_{GK} = \infty$; method 1 (linear voltage rise)	$T_{VJ} = 140^{\circ}\text{C}$		1000	V/ μs	
V_{GT}	gate trigger voltage	$V_D = 6\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$		1.5	V	
			$T_{VJ} = -40^{\circ}\text{C}$		1.6	V	
I_{GT}	gate trigger current	$V_D = 6\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$		150	mA	
			$T_{VJ} = -40^{\circ}\text{C}$		200	mA	
V_{GD}	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 140^{\circ}\text{C}$		0.2	V	
I_{GD}	gate non-trigger current				10	mA	
I_L	latching current	$t_p = 10\text{ }\mu\text{s}$	$T_{VJ} = 25^{\circ}\text{C}$		200	mA	
		$I_G = 0.45\text{ A}$; $di_G/dt = 0.45\text{ A}/\mu\text{s}$					
I_H	holding current	$V_D = 6\text{ V}$ $R_{GK} = \infty$	$T_{VJ} = 25^{\circ}\text{C}$		200	mA	
t_{gd}	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$	$T_{VJ} = 25^{\circ}\text{C}$		2	μs	
		$I_G = 0.45\text{ A}$; $di_G/dt = 0.45\text{ A}/\mu\text{s}$					
t_q	turn-off time	$V_R = 100\text{ V}$; $I_T = 110\text{ A}$; $V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 140^{\circ}\text{C}$		185	μs	
		$di/dt = 10\text{ A}/\mu\text{s}$; $dv/dt = 20\text{ V}/\mu\text{s}$; $t_p = 200\text{ }\mu\text{s}$					

Package TO-240AA				Ratings		
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			200	A
T_{VJ}	virtual junction temperature		-40		140	°C
T_{op}	operation temperature		-40		125	°C
T_{stg}	storage temperature		-40		125	°C
Weight					90	g
M_D	mounting torque		2.5		4	Nm
M_T	terminal torque		2.5		4	Nm
$d_{Spp/App}$	creepage distance on surface striking distance through air	terminal to terminal	13.0	9.7		mm
$d_{Spb/Apb}$		terminal to backside	16.0	16.0		mm
V_{ISOL}	isolation voltage	t = 1 second		4800		V
		t = 1 minute	50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA	4000		V


Part number

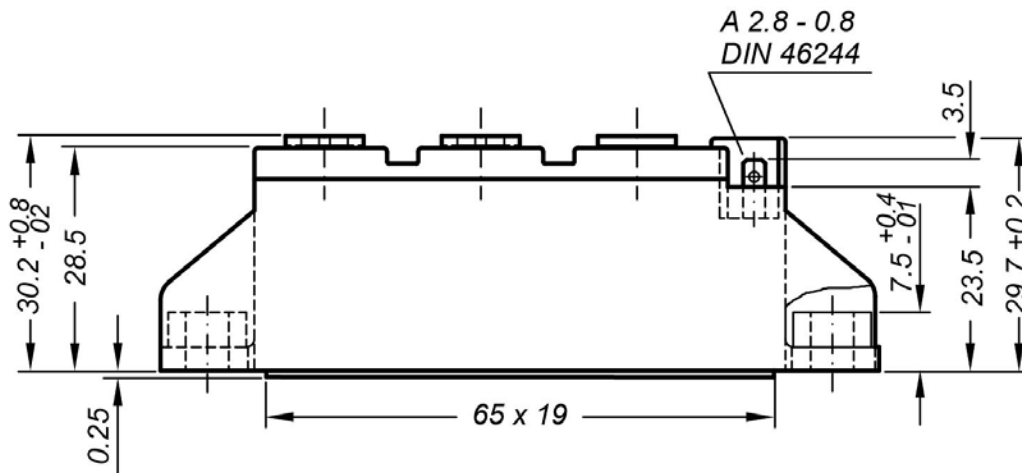
- M = Module
- C = Thyristor (SCR)
- M = Thyristor
- A = (up to 1800V)
- 110 = Current Rating [A]
- P = Phase leg
- 1200 = Reverse Voltage [V]
- TA = TO-240AA-1B

Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MCMA110P1200TA	MCMA110P1200TA	Box	6	513376

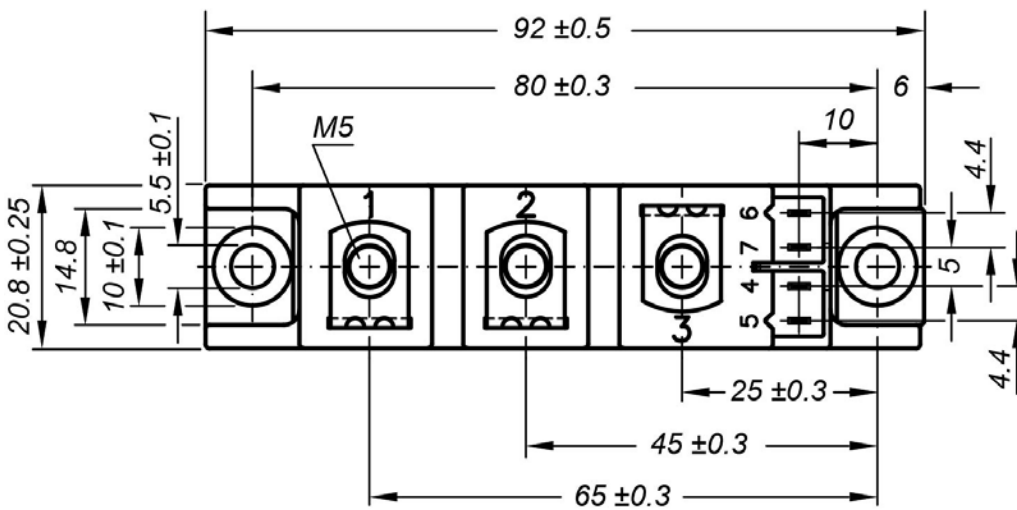
Equivalent Circuits for Simulation
** on die level*
 $T_{VJ} = 140\text{ °C}$

Thyristor

$V_{0\max}$	threshold voltage	0.85	V
$R_{0\max}$	slope resistance *	2.1	mΩ

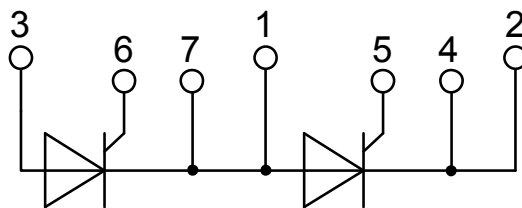
Outlines TO-240AA



General tolerance: DIN ISO 2768 class „c“



Optional accessories: Keyed gate/cathode twin plugs
 Wire length: 350 mm, gate = white, cathode = red
 UL 758, style 3751
 Type **ZY 200L** (L = Left for pin pair 4/5)
 Type **ZY 200R** (R = Right for pin pair 6/7)



Thyristor

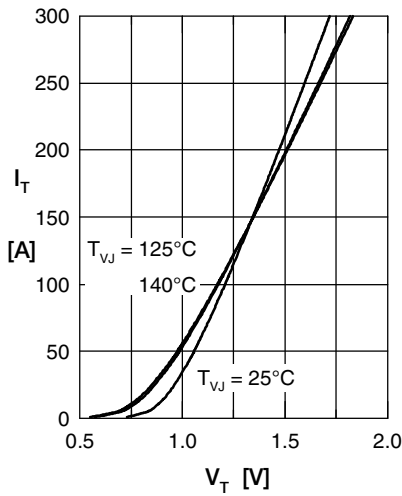


Fig. 1 Forward characteristics

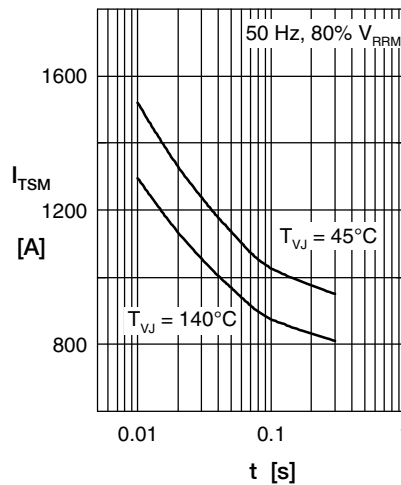


Fig. 2 Surge overload current
 I_{TSM} : crest value, t : duration

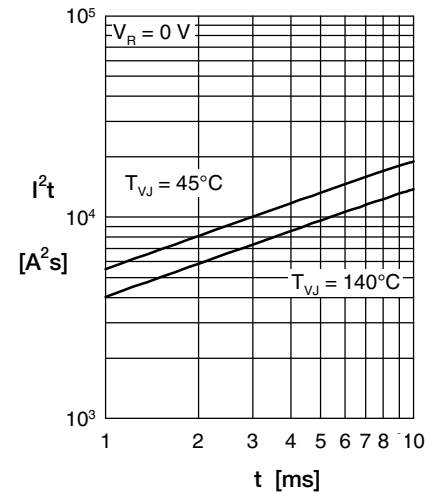


Fig. 3 I^2t versus time (1-10 s)

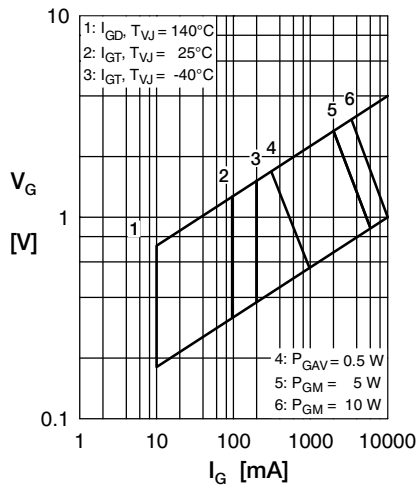


Fig. 4 Gate voltage & gate current

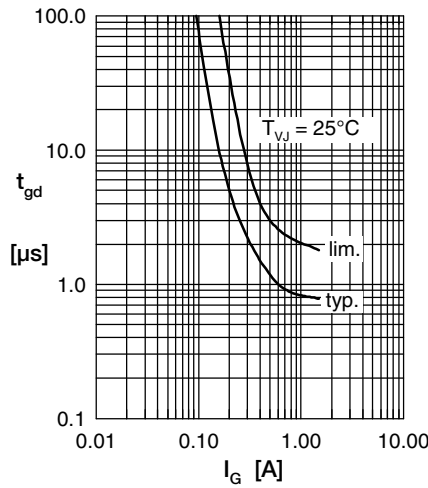


Fig. 5 Gate controlled delay time t_{gd}

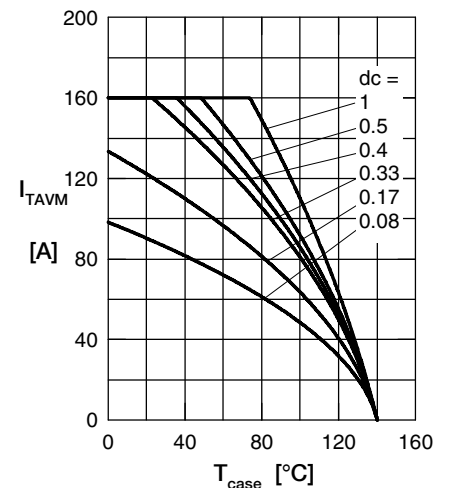


Fig. 6 Max. forward current at case temperature

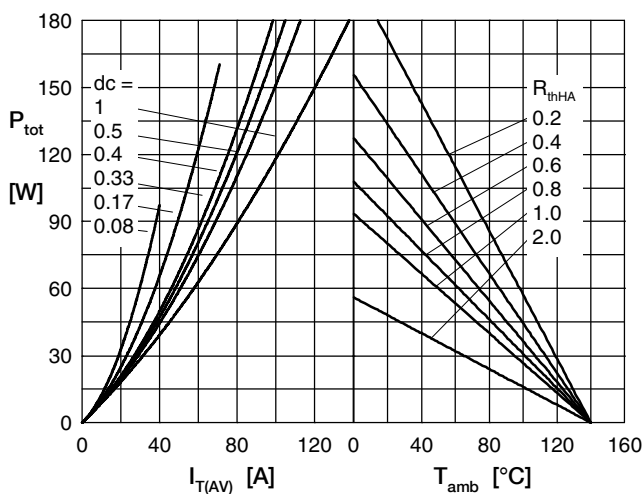


Fig. 7a Power dissipation versus direct output current
Fig. 7b and ambient temperature

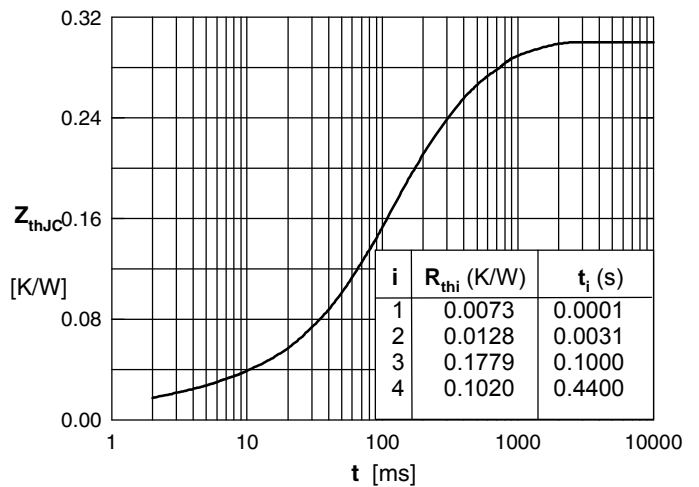


Fig. 8 Transient thermal impedance junction to case